

40V N-Channel MOSFET

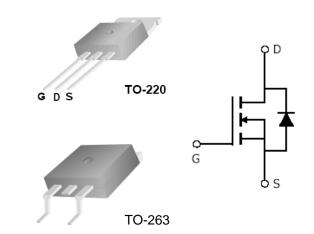
Applications:

- **Power Supply**
- **DC-DC Converters**

| V_{DSS} | R _{DS(ON)} (Max) | I_D^a |
|-----------|---------------------------|---------|
| 40 V | 4.0 mΩ | 173 A |

Features:

- LeadFree
- Low $R_{\text{DS(ON)}}$ to Minimize Conductive Loss Low Gate Change for Fast Switching Application
- Optimized B_{VDSS} Capability



Ordering Information

| Part Number | Package | Brand |
|-------------|---------|-------|
| MXP4004BT | TO220 | MXP |
| MXP4004BE | TO263 | MXP |

Absolute Maximum Ratings

T_c=25°C unless otherwise specified

| Symbol | Parameter | Value | Units |
|-------------------------------------|--|------------|------------------------|
| V _{DS} | Drain-to-Source Voltage | 40 | V |
| I _D ^a | Continuous Drain Current (T _C =25°ℂ) | 173 | ۸ |
| I _{DM} | Pulsed Drain Current @V _G =10V | 693 | А |
| E _{AS} | Single Pulse Avalanche Energy (L=1mH) | 724 | mJ |
| I _{AS} | Pulsed Avalanche Energy | Figure.9 | А |
| T _J and T _{STG} | Operating Junction and Storage Temperature Range | -55 to 175 | $^{\circ}\!\mathbb{C}$ |

a. Calculated continuous current based upon maximum allowable junction temperature, +175°C. Package limitation current is 80A.

OFF Characteristics

T_J=25°C unless otherwise specified

| Symbol | Parameter | Min | Тур | Max | Units | Test Conditions |
|-------------------|------------------------------------|-----|-----|-----|-------|---|
| BV _{DSS} | Drain-to-Source Breakdown Voltage | 40 | | | V | V _{GS} =0V, I _D =250μA |
| I _{DSS} | Drain-to-Source Leakage Current | | | 1 | μA | V _{DS} =32V, V _{GS} =0V |
| | | | | 100 | | V_{DS} =32V, V_{GS} =0V T_J =125 $^{\circ}$ C |
| I _{GSS} | Gate-to-Source Forward Leakage | | | 100 | nΛ | V _{GS} =+20V |
| | Gate-to-Source Reverse Leakage | | | 100 | ⊣ nA | V _{GS} = -20V |

ON Characteristics

T_J=25°C unless otherwise specified

| Symbol | Parameter | Min | Тур | Max | Units | Test Conditions |
|---------------------|---|-----|-----|-----|-------|--|
| R _{DS(ON)} | Static Drain-to-Source On-Resistance | | 2.5 | 4 | mΩ | V _{GS} = 10V, I _D =24A |
| $V_{GS(TH)}$ | Gate Threshold Voltage | 2 | | 4 | V | $V_{DS}=V_{GS}$, $I_{D}=250\mu A$ |

Dynamic CharacteristicsEssentially independent of operating temperature

| Symbol | Parameter | Min | Тур | Max | Units | Test Conditions |
|---------------------|------------------------------------|-----|------|-----|-------|--|
| C _{iss} | Input Capacitance | | 5016 | | | V _{GS} =0V, V _{DS} =20V, f=1.0MHz |
| Coss | Output Capacitance | | 787 | | pF | |
| C _{rss} | Reverse Transfer Capacitance | | 292 | | ' | |
| Qg | Total Gate Charge | | 70 | | nC | V _{DD} =20V, I _D =86A, V _G =10V |
| Q _{gs} | Gate-to-Source Charge | | 24 | | | |
| Q_{gd} | Gate-to-Drain ("Miller") Charge | | 24 | | | |
| t _{d(on)} | Turn-on Delay Time | | 19 | | | V_{DD} =20V, I_{D} =86A, V_{G} =10V, R_{G} =4.7 Ω |
| t _r | Rise Time | | 67 | | ns | |
| t _{d(off)} | Turn-off Delay Time | | 49 | | | |
| t _f | Fall Time | | 31 | | | |

Source-Drain Diode Characteristics

Tc=25°C unless otherwise specified

| Symbol | Parameter | Min | Тур | Max | Units | Test Conditions | |
|----------|----------------------------|-----|-----|-----|----------|--|--|
| V_{SD} | Diode Forward Voltage | | | 1.2 | V | I _S =24A, V _{GS} =0V | |
| Trr | Reverse Recovery Time | | 51 | 77 | ns | IS=38A, di/dt = 100A/μs | |
| Qrr | Reverse Recovery Charge | | 35 | 53 | nC | | |

Figure 1. Maximum Power Dissipation V.S

Case Temperature

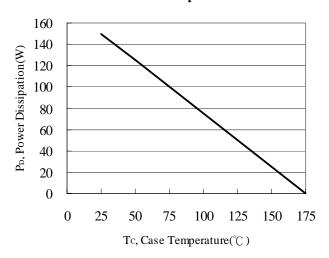


Figure 3. Typical Output Characteristics

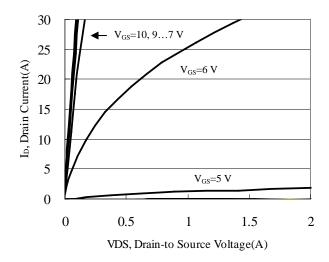


Figure 5. Threshold Voltage V.S Junction Temperature

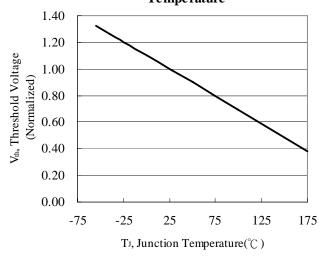


Figure 2. Maximum Continuous Drain Current V.S Case Temperature

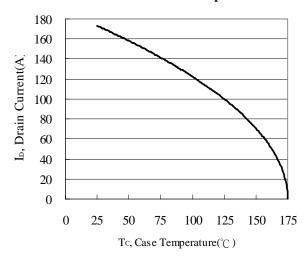


Figure 4. Breakdown Voltage V.S Junction Temperature

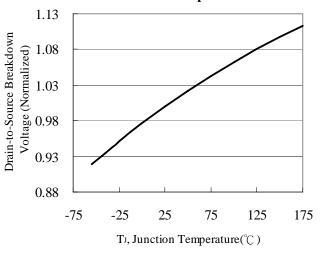


Figure 6. Drain-to-Source Resistance V.S Junction Temperature

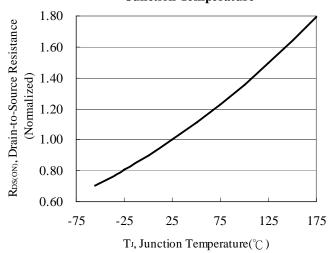


Figure 7. Typical Gate Charge vs. Gate-to-

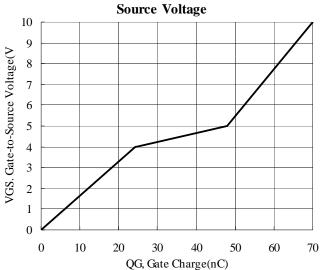


Figure 8. Typical Capacitance vs. Drain-to-

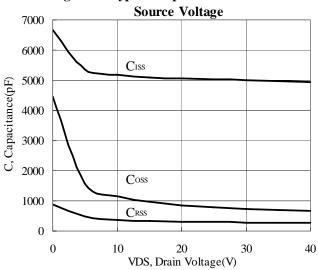


Figure 9. Unclamped Inductive Switching Capability

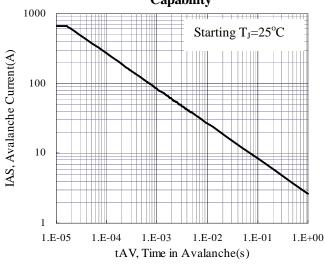
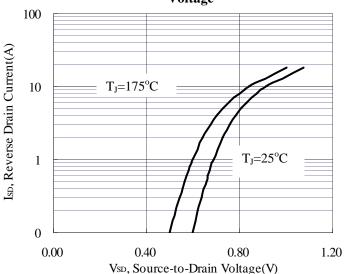


Figure 10. Source-Drain Diode Forward Voltage



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